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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	18
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 11x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1027aana-w5

1.3.2 On-chip oscillator characteristics

(1) High-speed on-chip oscillator oscillation frequency of the R5F102 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip oscillator oscillation frequency accuracy	$T_A = -20$ to $+85$ °C	-1.0	+1.0	%
	$T_A = -40$ to -20 °C	-1.5	+1.5	
	$T_A = +85$ to $+105$ °C	-2.0	+2.0	

(2) High-speed on-chip oscillator oscillation frequency of the R5F103 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip oscillator oscillation frequency accuracy	$T_A = -40$ to $+85$ °C	-5.0	+5.0	%

1.3.3 Peripheral Functions

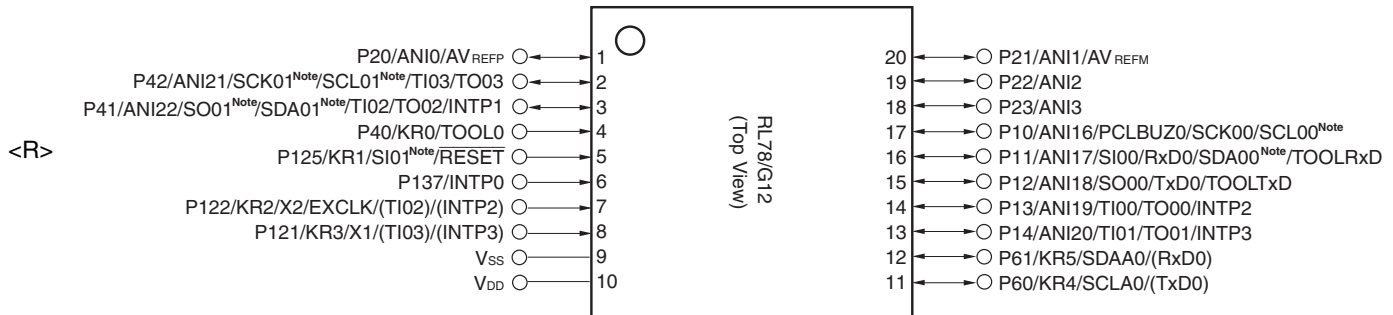
The following are differences in peripheral functions between the R5F102 products and the R5F103 products.

RL78/G12		R5F102 product		R5F103 product	
		20, 24 pin product	30 pin product	20, 24 pin product	30 pin product
Serial interface	UART	1 channel	3 channels	1 channel	
	CSI	2 channels	3 channels	1 channel	
	Simplified I ² C	2 channels	3 channels	None	
DMA function		2 channels		None	
Safety function	CRC operation	Yes		None	
	RAM guard	Yes		None	
	SFR guard	Yes		None	

1.4 Pin Configuration (Top View)

1.4.1 20-pin products

- 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)



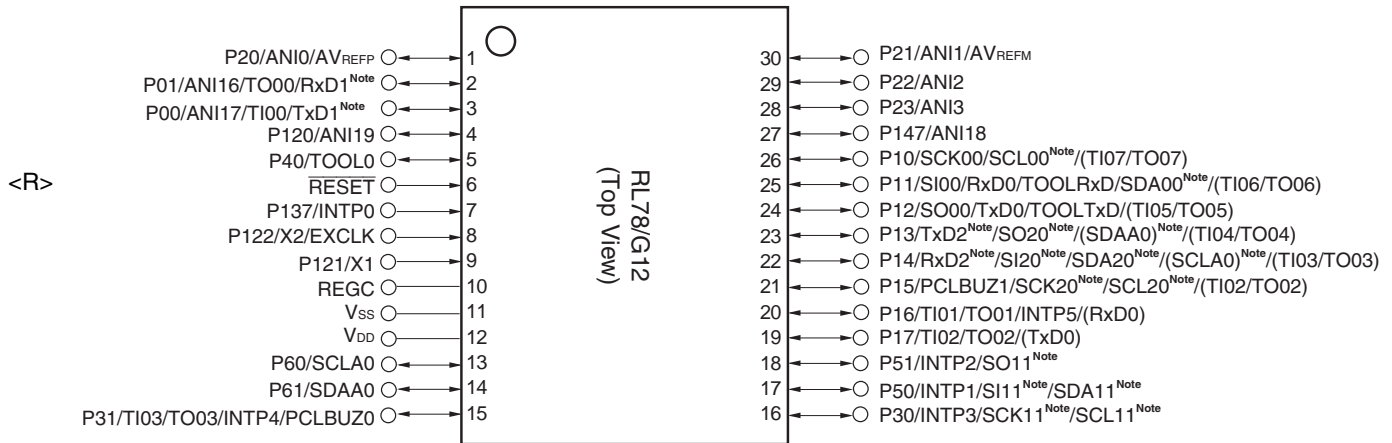
Note Provided only in the R5F102 products.

Remarks 1. For pin identification, see **1.5 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)**.

1.4.3 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Note Provided only in the R5F102 products.

Caution Connect the REGC pin to V_{SS} via capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see 1.5 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR).

1.7 Outline of Functions

This outline describes the function at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

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Item		20-pin		24-pin		30-pin	
		R5F1026x	R5F1036x	R5F1027x	R5F1037x	R5F102Ax	R5F103Ax
Code flash memory		2 to 16 KB ^{Note 1}		4 to 16 KB			
Data flash memory		2 KB	–	2 KB	–	2 KB	–
RAM		256 B to 1.5 KB		512 B to 1.5 KB		512 B to 2KB	
Address space		1 MB					
<R> Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode : 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode : 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode : 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V)					
	High-speed on-chip oscillator clock	HS (High-speed main) mode : 1 to 24 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode : 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode : 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V)					
Low-speed on-chip oscillator clock		15 kHz (TYP)					
General-purpose register		(8-bit register × 8) × 4 banks					
Minimum instruction execution time		0.04167 μ s (High-speed on-chip oscillator clock: $f_{IH} = 24$ MHz operation) 0.05 μ s (High-speed system clock: $f_{MX} = 20$ MHz operation)					
Instruction set		<ul style="list-style-type: none"> • Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (set, reset, test, and Boolean operation), etc. 					
I/O port	Total	18		22		26	
	CMOS I/O	12 (N-ch O.D. I/O [V_{DD} withstand voltage]: 4)		16 (N-ch O.D. I/O [V_{DD} withstand voltage]: 5)		21 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)	
	CMOS input	4		4		3	
	N-ch open-drain I/O (6 V tolerance)	2					
Timer	16-bit timer	4 channels				8 channels	
	Watchdog timer	1 channel					
	12-bit Interval timer	1 channel					
	Timer output	4 channels (PWM outputs: 3 ^{Note 3})				8 channels (PWM outputs: 7 ^{Note 3} , ^{Note 2})	

Notes 1. The self-programming function cannot be used in the R5F10266 and R5F10366.

2. The maximum number of channels when PIOR0 is set to 1.

3. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves). (See 6.9.3 Operation as multiple PWM output function.)

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

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Item	20-pin		24-pin		30-pin		
	R5F1026x	R5F1036x	R5F1027x	R5F1037x	R5F102Ax	R5F103Ax	
Clock output/buzzer output	1				2		
	2.44 kHz to 10 MHz: (Peripheral hardware clock: $f_{\text{MAIN}} = 20$ MHz operation)						
8/10-bit resolution A/D converter	11 channels				8 channels		
Serial interface	[R5F1026x (20-pin), R5F1027x (24-pin)]						
	• CSI: 2 channels/Simplified I ² C: 2 channels/UART: 1 channel						
	[R5F102Ax (30-pin)]						
	• CSI: 1 channel/Simplified I ² C: 1 channel/UART: 1 channel						
Serial interface	• CSI: 1 channel/Simplified I ² C: 1 channel/UART: 1 channel						
	• CSI: 1 channel/Simplified I ² C: 1 channel/UART: 1 channel						
Serial interface	[R5F1036x (20-pin), R5F1037x (24-pin)]						
	• CSI: 1 channel/Simplified I ² C: 0 channel/UART: 1 channel						
Serial interface	[R5F103Ax (30-pin)]						
	• CSI: 1 channel/Simplified I ² C: 0 channel/UART: 1 channel						
	I ² C bus	1 channel					
Multiplier and divider/multiply-accumulator	<ul style="list-style-type: none"> • 16 bits × 16 bits = 32 bits (unsigned or signed) • 32 bits × 32 bits = 32 bits (unsigned) • 16 bits × 16 bits + 32 bits = 32 bits (unsigned or signed) 						
DMA controller	2 channels	—	2 channels	—	2 channels	—	
Vectored interrupt sources	Internal	18	16	18	16	26	19
	External	5				6	
Key interrupt	6		10		—		
Reset	<ul style="list-style-type: none"> • Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution ^{Note} • Internal reset by RAM parity error • Internal reset by illegal-memory access 						
Power-on-reset circuit	<ul style="list-style-type: none"> • Power-on-reset: 1.51 V (TYP) • Power-down-reset: 1.50 V (TYP) 						
Voltage detector	<ul style="list-style-type: none"> • Rising edge : 1.88 to 4.06 V (12 stages) • Falling edge : 1.84 to 3.98 V (12 stages) 						
On-chip debug function	Provided						
Power supply voltage	$V_{\text{DD}} = 1.8$ to 5.5 V						
Operating ambient temperature	$T_{\text{A}} = -40$ to $+85^{\circ}\text{C}$ (A: Consumer applications, D: Industrial applications), $T_{\text{A}} = -40$ to $+105^{\circ}\text{C}$ (G: Industrial applications)						

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2.2 Oscillator Characteristics

2.2.1 X1 oscillator characteristics

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f _x) ^{Note}	Ceramic resonator / crystal oscillator	2.7 V ≤ V _{DD} ≤ 5.5 V	1.0		20.0	MHz
		1.8 V ≤ V _{DD} < 2.7 V	1.0		8.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to **5.4 System Clock Oscillator**.

2.2.2 On-chip oscillator characteristics

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit	
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	f _H		1		24	MHz	
High-speed on-chip oscillator clock frequency accuracy		R5F102 products	T _A = -20 to +85°C	-1.0		+1.0	%
			T _A = -40 to -20°C	-1.5		+1.5	%
		R5F103 products	-5.0		+5.0	%	
Low-speed on-chip oscillator clock frequency	f _L			15		kHz	
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%	

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

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Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	I _{OL1}	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147			20.0 <small>Note 2</small>	mA
		Per pin for P60, P61			15.0 <small>Note 2</small>	mA
		20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V		60.0	mA
			2.7 V ≤ V _{DD} < 4.0 V		9.0	mA
			1.8 V ≤ V _{DD} < 2.7 V		1.8	mA
		20-, 24-pin products: Total of P00 to P03 ^{Note 4} , P10 to P14, P60, P61 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V		80.0	mA
			2.7 V ≤ V _{DD} < 4.0 V		27.0	mA
			1.8 V ≤ V _{DD} < 2.7 V		5.4	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})			140	mA
		I _{OL2}	Per pin for P20 to P23			0.4
Total of all pins				1.6	mA	

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

2. However, do not exceed the total current value.
3. The output current value under conditions where the duty factor ≤ 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA

$$\text{Total output current of pins} = (10.0 \times 0.7)/(80 \times 0.01) \cong 8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) 30-pin products

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current ^{Note 1}	I _{DD2} ^{Note 2}	HALT mode	HS (High-speed main) mode ^{Note 6}	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	1280	μA
					V _{DD} = 3.0 V		440	1280	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1000	μA
					V _{DD} = 3.0 V		400	1000	
			LS (Low-speed main) mode ^{Note 6}	f _{IH} = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		260	530	μA
					V _{DD} = 2.0 V		260	530	
			HS (High-speed main) mode ^{Note 6}	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		280	1000	μA
					Resonator connection		450	1170	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		280	1000	μA
					Resonator connection		450	1170	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		190	600	μA
					Resonator connection		260	670	
			f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		190	600	μA	
				Resonator connection		260	670		
	LS (Low-speed main) mode ^{Note 6}	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		95	330	μA		
			Resonator connection		145	380			
f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 2.0 V		Square wave input		95	330	μA			
		Resonator connection		145	380				
I _{DD3} ^{Note 5}	STOP mode	T _A = -40°C					0.18	0.50	μA
		T _A = +25°C					0.23	0.50	
		T _A = +50°C					0.30	1.10	
		T _A = +70°C					0.46	1.90	
		T _A = +85°C					0.75	3.30	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.
3. When high-speed on-chip oscillator clock is stopped.
4. When high-speed system clock is stopped.
5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @ 1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @ 1 MHz to 16 MHz

LS (Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @ 1 MHz to 8 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency
3. Except STOP mode, temperature condition of the TYP. value is T_A = 25°C.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)**(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit		
			MIN.	MAX.	MIN.	MAX.			
Transfer rate <small>Note4</small>		Reception	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V		f _{MCK} /6 <small>Note1</small>		f _{MCK} /6 <small>Note1</small>	bps	
			Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} <small>Note3</small>		4.0		1.3	Mbps	
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V			f _{MCK} /6 <small>Note1</small>		f _{MCK} /6 <small>Note1</small>	bps
				Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} <small>Note3</small>		4.0		1.3	Mbps
			1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V			f _{MCK} /6 <small>Notes1, 2</small>		f _{MCK} /6 <small>Notes1, 2</small>	bps
				Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} <small>Note3</small>		4.0		1.3	Mbps
		Transmission	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V			Note4		Note4	bps
				Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 1.4 kΩ, V _b = 2.7 V		2.8 <small>Note5</small>		2.8 <small>Note5</small>	Mbps
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V,			Note6		Note6	bps
				Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 2.7 kΩ, V _b = 2.3 V		1.2 <small>Note7</small>		1.2 <small>Note7</small>	Mbps
1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V				Notes 2, 8		Notes 2, 8	bps		
	Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 5.5 kΩ, V _b = 1.6 V			0.43 <small>Note9</small>		0.43 <small>Note9</small>	Mbps		

- Notes**
- Transfer rate in the SNOOZE mode is 4800 bps only.
 - Use it with V_{DD} ≥ V_b.
 - The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
 HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
 16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
 LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
 - The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
 Expression for calculating the transfer rate when 4.0 V ≤ V_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \quad [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

5. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 4** above to calculate the maximum transfer rate under conditions of the customer.

6. The smaller maximum transfer rate derived by using $f_{mck}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$ and $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \quad [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

7. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 6** above to calculate the maximum transfer rate under conditions of the customer.

8. The smaller maximum transfer rate derived by using $f_{mck}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $1.8\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \quad [\text{bps}]$$

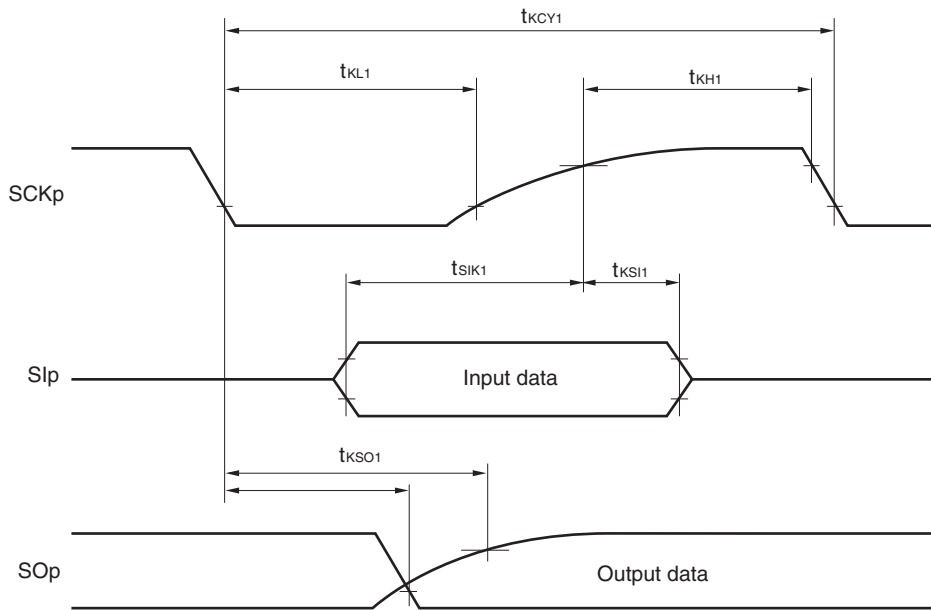
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

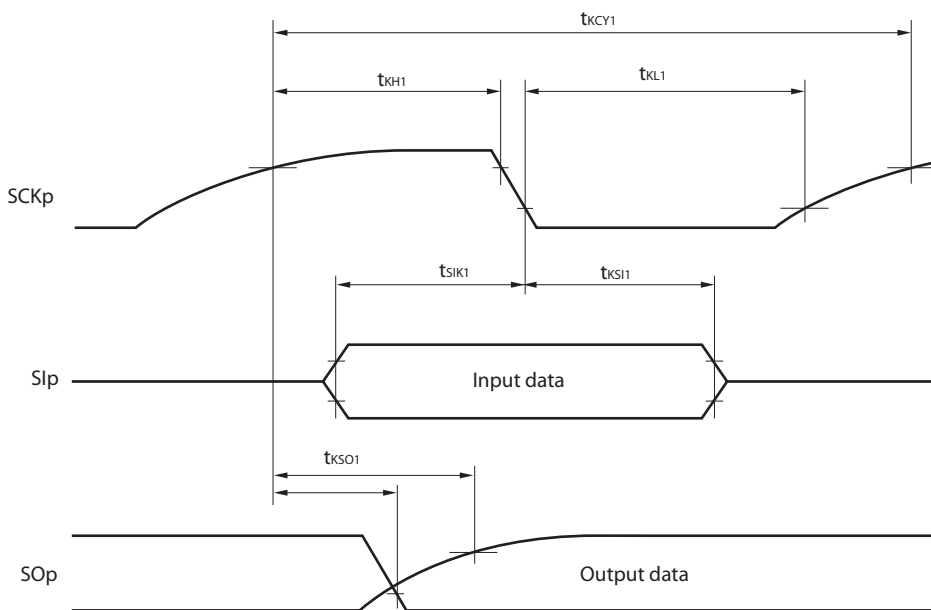
9. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 8** above to calculate the maximum transfer rate under conditions of the customer.

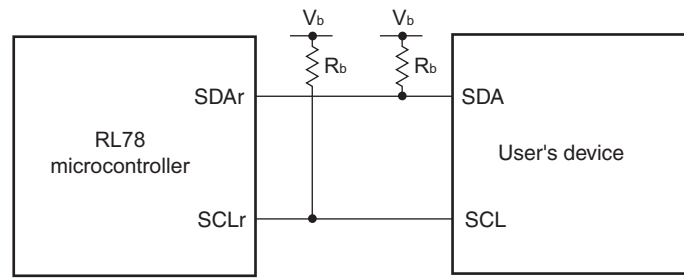
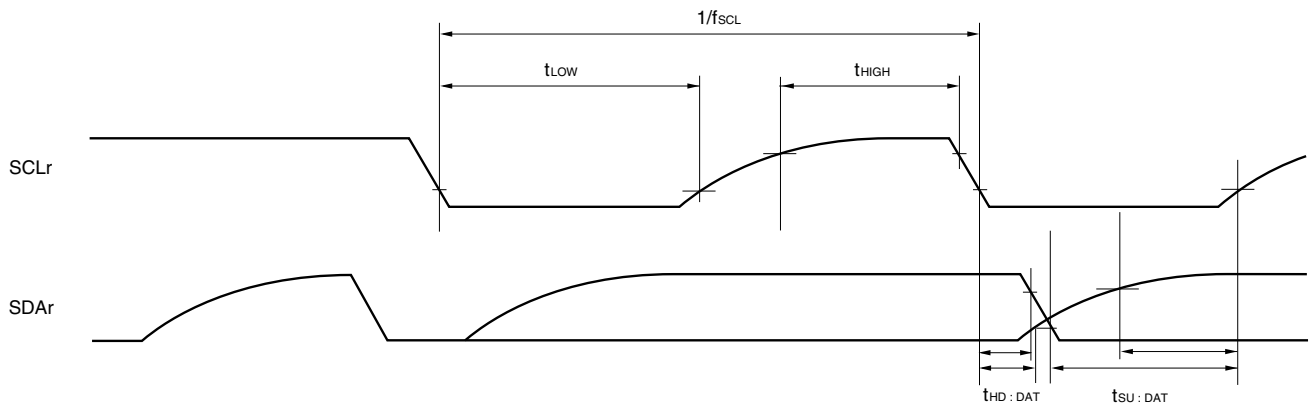
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). **For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.**

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Simplified I²C mode connection diagram (during communication at different potential)**Simplified I²C mode serial transfer timing (during communication at different potential)**

- Remarks 1.** R_b [Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b [F]: Communication line (SDAr, SCLr) load capacitance, V_b [V]: Communication line voltage
- 2.** r: IIC Number (r = 00, 20)
- 3.** f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number (m = 0,1), n: Channel number (n = 0))
- 4.** Simplified I²C mode is supported only by the R5F102 products.

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(2/4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	I _{OL1}	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147			8.5 <small>Note 2</small>	mA
		Per pin for P60, P61			15.0 <small>Note 2</small>	mA
		20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V		25.5	mA
			2.7 V ≤ V _{DD} < 4.0 V		9.0	mA
			2.4 V ≤ V _{DD} < 2.7 V		1.8	mA
		20-, 24-pin products: Total of P00 to P03 ^{Note 4} , P10 to P14, P60, P61 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V		40.0	mA
			2.7 V ≤ V _{DD} < 4.0 V		27.0	mA
			2.4 V ≤ V _{DD} < 2.7 V		5.4	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})			65.5	mA
		I _{OL2}	Per pin for P20 to P23			0.4
Total of all pins				1.6	mA	

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA

$$\text{Total output current of pins} = (10.0 \times 0.7)/(80 \times 0.01) \cong 8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(1) 20-, 24-pin products

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(1/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit		
Supply current ^{Note 1}	I _{DD1}	Operating mode	HS (High-speed main) mode ^{Note 4}	f _{IH} = 24 MHz ^{Note 3}	Basic operation	V _{DD} = 5.0 V		1.5		mA	
						V _{DD} = 3.0 V		1.5			
					Normal operation	V _{DD} = 5.0 V		3.3	5.3	mA	
						V _{DD} = 3.0 V		3.3	5.3		
						V _{DD} = 5.0 V		2.5	3.9		mA
						V _{DD} = 3.0 V		2.5	3.9		
				f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input		2.8	4.7	mA		
					Resonator connection		3.0	4.8			
				f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input		2.8	4.7	mA		
					Resonator connection		3.0	4.8			
				f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input		1.8	2.8	mA		
					Resonator connection		1.8	2.8			
f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input		1.8	2.8	mA						
	Resonator connection		1.8	2.8							

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- When high-speed on-chip oscillator clock is stopped.
- When high-speed system clock is stopped
- Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: V_{DD} = 2.7 V to 5.5 V @ 1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @ 1 MHz to 16 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

- f_{IH}: high-speed on-chip oscillator clock frequency
- Temperature condition of the TYP. value is T_A = 25°C.

3.4 AC Characteristics

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	TCY	Main system clock (fMAIN) operation	HS (High-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.04167	1	μs
				2.4 V ≤ VDD < 2.7 V	0.0625	1	μs
		During self programming	HS (High-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.04167	1	μs
				2.4 V ≤ VDD < 2.7 V	0.0625	1	μs
External main system clock frequency	fEX	2.7 V ≤ VDD ≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ VDD < 2.7 V		1.0		16.0	MHz
External main system clock input high-level width, low-level width	tEXH, tEXL	2.7 V ≤ VDD ≤ 5.5 V		24			ns
		2.4 V ≤ VDD < 2.7 V		30			ns
TI00 to TI07 input high-level width, low-level width	tTIH, tTIL			1/fMCK + 10			ns
TO00 to TO07 output frequency	fTO	4.0 V ≤ VDD ≤ 5.5 V				12	MHz
		2.7 V ≤ VDD < 4.0 V				8	MHz
		2.4 V ≤ VDD < 2.7 V				4	MHz
PCLBUZ0, or PCLBUZ1 output frequency	fPCL	4.0 V ≤ VDD ≤ 5.5 V				16	MHz
		2.7 V ≤ VDD < 4.0 V				8	MHz
		2.4 V ≤ VDD < 2.7 V				4	MHz
INTP0 to INTP5 input high-level width, low-level width	tINTH, tINTL			1			μs
KR0 to KR9 input available width	tKR			250			ns
RESET low-level width	tRSL			10			μs

Remark fMCK: Timer array unit operation clock frequency
 (Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

(4) During communication at same potential (simplified I²C mode)

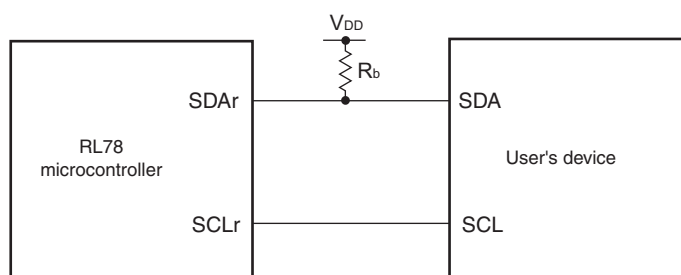
(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f _{SCL}	C _b = 100 pF, R _b = 3 kΩ		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	t _{LOW}	C _b = 100 pF, R _b = 3 kΩ	4600		ns
Hold time when SCLr = "H"	t _{HIGH}	C _b = 100 pF, R _b = 3 kΩ	4600		ns
Data setup time (reception)	t _{SU:DAT}	C _b = 100 pF, R _b = 3 kΩ	1/f _{MCK} + 580 ^{Note 2}		ns
Data hold time (transmission)	t _{HD:DAT}	C _b = 100 pF, R _b = 3 kΩ	0	1420	ns

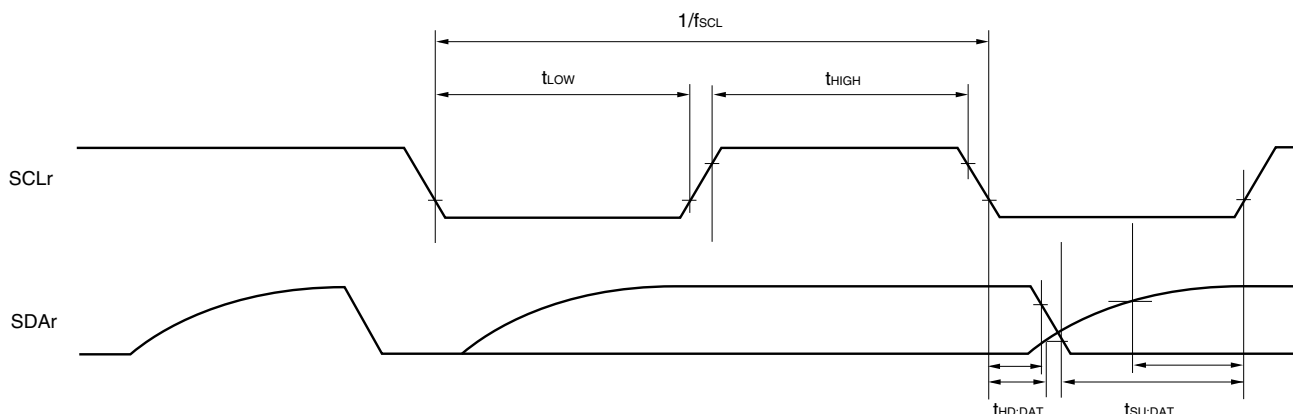
- Notes**
- The value must also be equal to or less than f_{MCK}/4.
 - Set t_{SU:DAT} so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Caution Select the N-ch open drain output (V_{DD} tolerance) mode for SDAr by using port output mode register h (POMh).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- Remarks**
- R_b [Ω]: Communication line (SDAr) pull-up resistance
C_b [F]: Communication line (SCLr, SDAr) load capacitance
 - r: IIC number (r = 00, 01, 11, 20), h: = POM number (h = 0, 1, 4, 5)
 - f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number (m = 0, 1), n: Channel number (0, 1, 3))

3.5.2 Serial interface IICA

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode				Unit
			Standard Mode		Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode: f _{CLK} ≥ 3.5 MHz			0	400	kHz
		Normal mode: f _{CLK} ≥ 1 MHz	0	100			
Setup time of restart condition	t _{SU:STA}		4.7		0.6		μs
Hold time ^{Note 1}	t _{HD:STA}		4.0		0.6		μs
Hold time when SCLA0 = "L"	t _{LOW}		4.7		1.3		μs
Hold time when SCLA0 = "H"	t _{HIGH}		4.0		0.6		μs
Data setup time (reception)	t _{SU:DAT}		250		100		ns
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}		0	3.45	0	0.9	μs
Setup time of stop condition	t _{SU:STO}		4.0		0.6		μs
Bus-free time	t _{BUF}		4.7		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

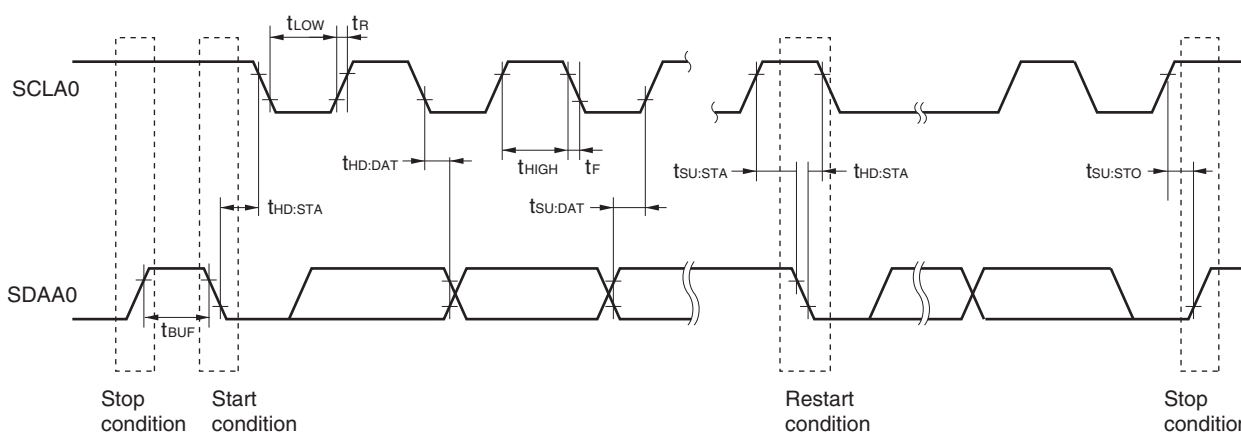
<R> **2.** The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Normal mode: C_b = 400 pF, R_b = 2.7 kΩ
 Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

IICA serial transfer timing

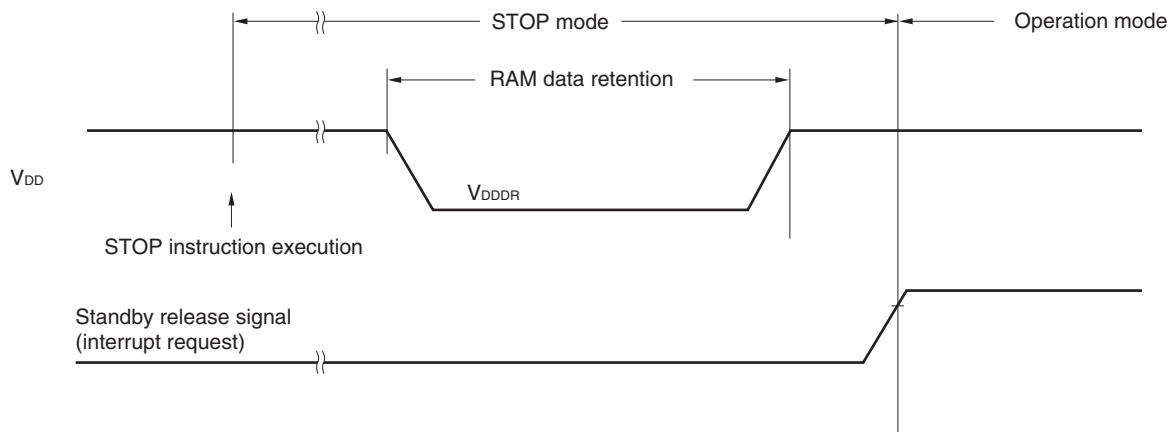


<R> 3.7 RAM Data Retention Characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 ^{Note}		5.5	V

<R> Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.8 Flash Memory Programming Characteristics

($T_A = -40$ to $+105^\circ\text{C}$, 2.4 V $\leq V_{DD} \leq 5.5$ V, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}		1		24	MHz
Code flash memory rewritable times <small>Notes 1, 2, 3</small>	C_{erwr}	Retained for 20 years $T_A = 85^\circ\text{C}$ ^{Notes 4}	1,000			Times
Data flash memory rewritable times <small>Notes 1, 2, 3</small>		Retained for 1 year $T_A = 25^\circ\text{C}$ ^{Notes 4}		1,000,000		
		Retained for 5 years $T_A = 85^\circ\text{C}$ ^{Notes 4}	100,000			
		Retained for 20 years $T_A = 85^\circ\text{C}$ ^{Notes 4}	10,000			

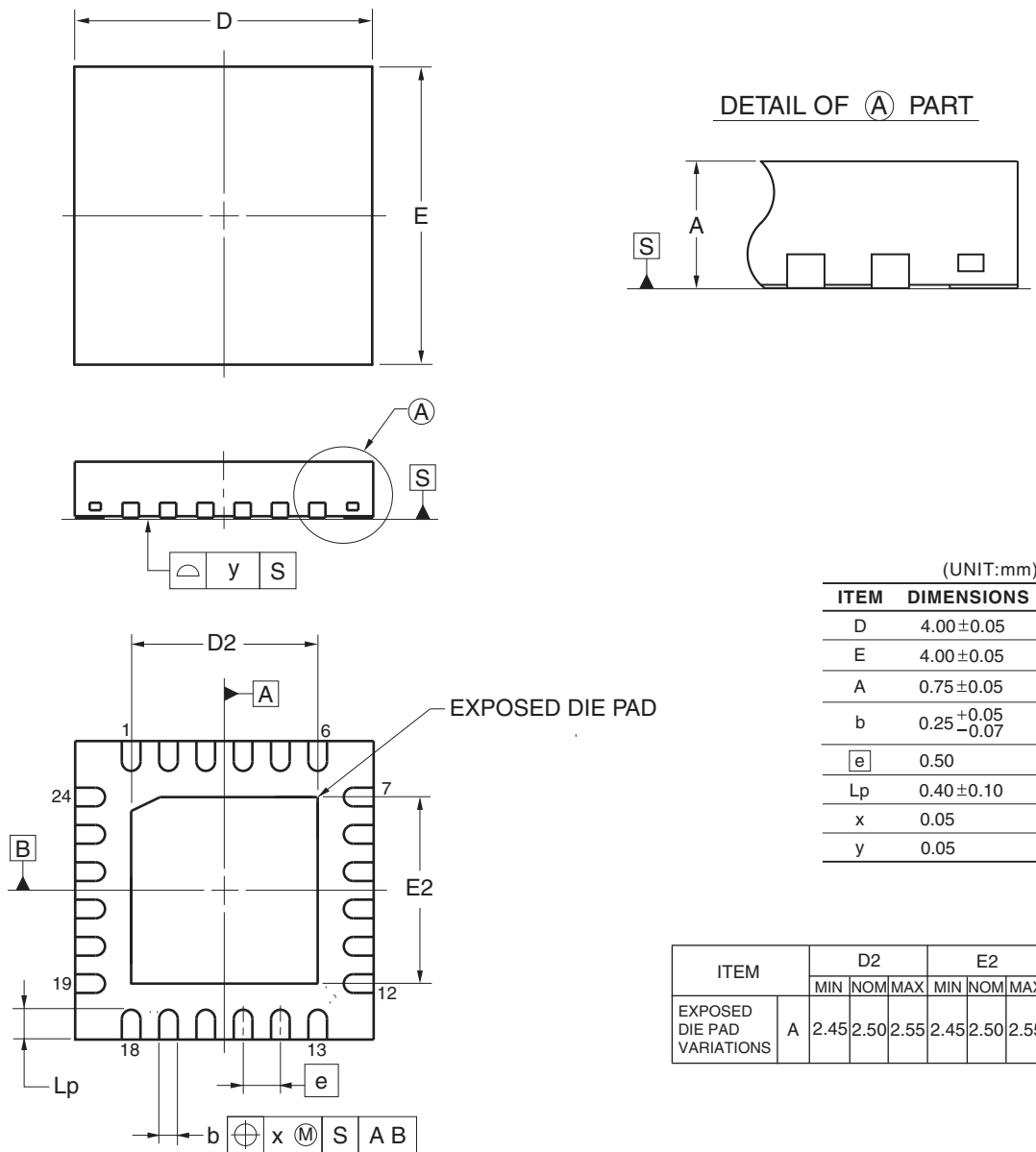
- Notes**
- 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 2. When using flash memory programmer and Renesas Electronics self programming library
 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 4. This temperature is the average value at which data are retained.

4.2 24-pin products

R5F1027AANA, R5F10279ANA, R5F10278ANA, R5F10277ANA
 R5F1037AANA, R5F10379ANA, R5F10378ANA, R5F10377ANA
 R5F1027ADNA, R5F10279DNA, R5F10278DNA, R5F10277DNA
 R5F1037ADNA, R5F10379DNA, R5F10378DNA, R5F10377DNA
 R5F1027AGNA, R5F10279GNA, R5F10278GNA, R5F10277GNA

<R>

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-1	0.04



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